Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A position-sensitive detector for measuring charged particles comprising a crystalline substrate and a surface region, the surface region comprising an amorphous layer with a structured, metallic layer disposed above it, wherein the structure of the metallic layer continues through the amorphous layer and at least partially into the crystalline substrate.

2. (Canceled)

- 3. (Previously Presented) The position-sensitive detector according to claim 1, wherein the amorphous layer is formed from germanium or silicon.
- 4. (Previously Presented) The position-sensitive detector according to claim 1, wherein the metallic layer comprises aluminium, palladium or gold.
- 5. (Previously Presented) The position-sensitive detector according to claim 1, wherein the substrate is formed of germanium, silicon or a III-V compound.
- 6. (Previously Presented) The position-sensitive detector according to claim 1, wherein the structure of the metallic layer is formed from segments having a mutual spacing of less than $200 \ \mu m$.
- 7. (Previously Presented) The position-sensitive detector according to claim 1, wherein the amorphous layer is disposed on a semiconductor material.
- 8. (Previously Presented) The position-sensitive detector according to claim 3, wherein the amorphous layer is not doped.

- 9. (Previously Presented) Tomograph or Compton camera with a detector according to claim 1.
- 10. (Previously Presented) The position-sensitive detector according to claim 6, wherein the mutual spacing is less than 100 μm .
- 11. (Previously Presented) The position-sensitive detector according to claim 6, wherein the mutual spacing is less than 20 μ m.
- 12. (Currently Amended) A method of producing a position-sensitive detector for measuring charged particles, comprising:

providing a crystalline substrate;

disposing on the substrate an amorphous Gallium Germanium layer;

disposing on the amorphous Gallium Germanium layer a metallic layer;

removing portions of the metallic layer, the amorphous Gallium Germanium layer and the crystalline substrate such that at least one structured electrode is formed.